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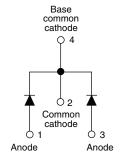
Vishay Semiconductors

COMPLIANT

Ultrafast Rectifier, 2 x 3 A FRED Pt®



D-PAK (TO-252AA)



PRODUCT SUMMARY					
Package	D-PAK (TO-252AA)				
I _{F(AV)}	2 x 3 A				
V _R	200 V				
V _F at I _F	1.0 V				
t _{rr} typ.	See Recovery table				
T _J max.	175 °C				
Diode variation	Common cathode				

FEATURES

- · Ultrafast recovery time
- · Low forward voltage drop
- Low leakage current
- 175 °C operating junction temperature
- Compliant to RoHS Directive 2002/95/EC
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C

DESCRIPTION/APPLICATIONS

VS-MURD620CTPbF is the state of the art ultrafast recovery rectifier specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS			
Peak repetitive reverse voltage	V_{RRM}		200	V			
Average rectified forward current per device	I _{F(AV)}	Total device, rated V _R , T _C = 146 °C	6				
Non-repetitive peak surge current	I _{FSM}		50	Α			
Peak repetitive forward current per diode	I _{FM}	Rated V _R , square wave, 20 kHz, T _C = 146 °C	6				
Operating junction and storage temperatures	T _J , T _{Stg}		- 65 to 175	°C			

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V _{BR} , V _R	Ι _R = 100 μΑ	200	-	-		
		I _F = 3 A	-	-	1.0		
Forward voltage	V _F	I _F = 3 A, T _J = 125 °C	-	-	0.96	V	
		I _F = 6 A	-	-	1.2		
		I _F = 6 A, T _J = 125 °C	-	-	1.13		
Б	I _R	V _R = V _R rated	-	-	5		
Reverse leakage current		$T_J = 125 ^{\circ}\text{C}$, $V_R = V_R$ rated		250	μA		
Junction capacitance	C _T	V _R = 200 V	-	12	-	pF	
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH	

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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS		
Reverse recovery time		$I_F = 1.0 \text{ A}, dI_F/dt = 50 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	-	35		
		I _F = 0.5 A, I _R = 1.0 A, I _{REC} = 0.25 A		-	-	25	ns	
	t _{rr}	T _J = 25 °C	I _F = 3 A dI _F /dt = 200 A/μs	-	19	-	115	
		T _J = 125 °C		-	26	-		
Peak recovery current	IRRM -	T _J = 25 °C		-	3.1	-	Α	
		T _J = 125 °C	V _R = 160 V	-	4.6	-	A	
Reverse recovery charge	Q _{rr}	T _J = 25 °C		-	30	-	20	
		T _J = 125 °C		-	60	-	nC	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T _J , T _{Stg}		- 65	-	175	°C	
Thermal resistance, junction to case per leg	R _{thJC}		-	-	9.0		
Thermal resistance, junction to ambient per leg	R _{thJA}		-	-	80	°C/W	
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	-	-		
Majaht			-	0.3	-	g	
Weight			-	0.01	-	OZ.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Marking device		Case style D-PAK		MURD	620CT		



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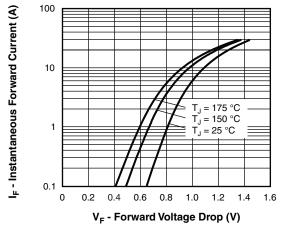


Fig. 1 - Typical Forward Voltage Drop Characteristics

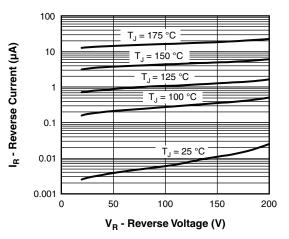


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

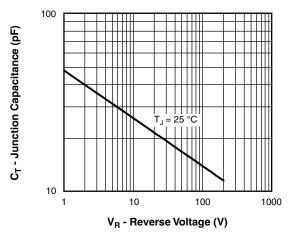


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

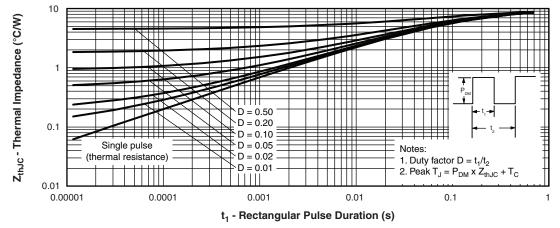


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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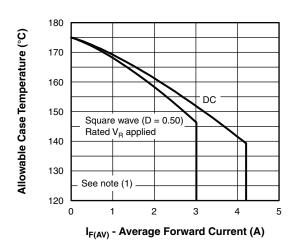


Fig. 5 - Maximum Allowable Case Temperature vs.
Average Forward Current

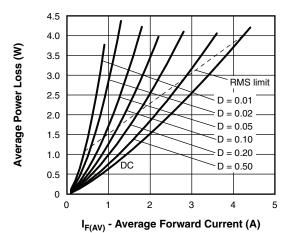


Fig. 6 - Forward Power Loss Characteristics

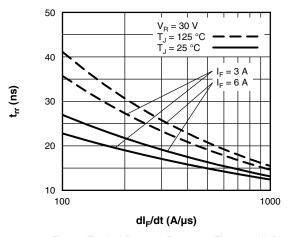


Fig. 7 - Typical Reverse Recovery Time vs. dI_F/dt

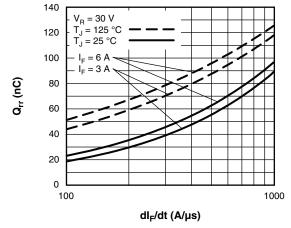


Fig. 8 - Typical Stored Charge vs. dl_F/dt

Note

 $\begin{array}{ll} \text{(1)} & \text{Formula used: } T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 6)}; \\ Pd_{REV} = \text{Inverse power loss} = V_{R1} \times I_R \text{ (1 - D); } I_R \text{ at } V_{R1} = \text{Rated } V_R \\ \end{array}$



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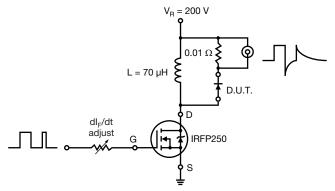
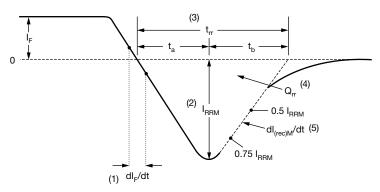


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl_F/dt rate of change of current through zero crossing
- (2) ${\rm I}_{\rm RRM}$ peak reverse recovery current
- (3) $t_{\rm rr}$ reverse recovery time measured from zero crossing point of negative going $I_{\rm F}$ to point where a line passing through 0.75 $I_{\rm RRM}$ and 0.50 $I_{\rm RRM}$ extrapolated to zero current.
- (4) Q_{rr} area under curve defined by t_{rr} and I_{BBM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) dl_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

VS-MURD620CTPbF

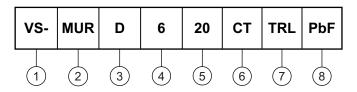
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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Ultrafast MUR series

3 - D = D-PAK

Current rating (6 = 6 A)

5 - Voltage rating (20 = 200 V)

- CT = Center tap (dual) TR = Tape and reel

TRL = Tape and reel (left oriented)
TRR = Tape and reel (right oriented)

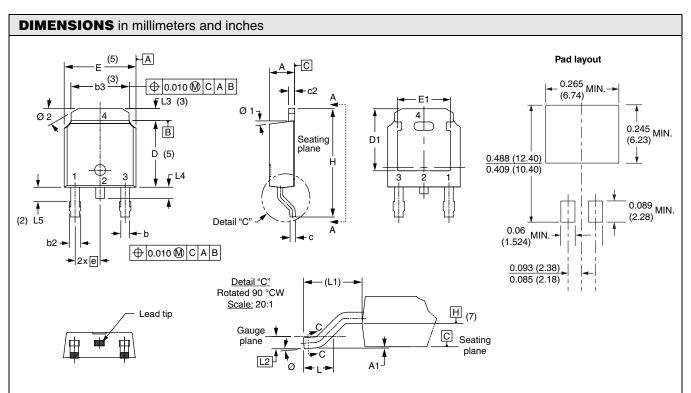
8 - PbF = Lead (Pb)-free

LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?95016</u>					
Part marking information	www.vishay.com/doc?95059				
Packaging information	www.vishay.com/doc?95033				



Vishay High Power Products

D-PAK (TO-252AA)



	MILLIMETERS		INCHES		
SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	2.18	2.39	0.086	0.094	
A1	-	0.13	-	0.005	
b	0.64	0.89	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	3
С	0.46	0.61	0.018	0.024	
c2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	5
D1	5.21	-	0.205	-	3
Е	6.35	6.73	0.250	0.265	5
E1	4.32	-	0.170	-	3

SYMBOL	MILLIM	MILLIMETERS		INCHES		
STINIBUL	MIN.	MAX.	MIN.	MAX.	NOTES	
е	2.29 BSC		0.090	BSC		
Н	9.40	10.41	0.370	0.410		
L	1.40	1.78	0.055	0.070		
L1	2.74 BSC		0.108 REF.			
L2	0.51	0.51 BSC		0.020 BSC		
L3	0.89	1.27	0.035	0.050	3	
L4	-	1.02	-	0.040		
L5	1.14	1.52	0.045	0.060	2	
Ø	0°	10°	0°	10°		
Ø1	0°	15°	0°	15°		
Ø2	25°	35°	25°	35°		

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension uncontrolled in L5
- (3) Dimension D1, E1, L3 and b3 establish a minimum mounting surface for thermal pad
- (4) Section C C dimension apply to the flat section of the lead between 0.13 and 0.25 mm (0.005 and 0.10") from the lead tip
- (5) Dimension D, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (6) Dimension b1 and c1 applied to base metal only
- $^{(7)}$ Datum A and B to be determined at datum plane H
- (8) Outline conforms to JEDEC outline TO-252AA



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